

10/051678

## ABSTRACT OF THE DISCLOSURE

A method of forming integrated circuitry includes chemical vapor depositing a silicon carbide comprising layer over a substrate at a temperature of no greater than 500°C. Plasma etching is conducted through at least a portion of the silicon carbide comprising layer using a gas chemistry comprising oxygen and hydrogen. Semiconductor processing methods include the above in fabrication of contact openings and in fabrication of MRAM circuitry. Semiconductor processing methods also include fabrication of contact openings using resist and removing silicon carbide comprising material and resist in a common plasma etching step.

10051678-011602